# 4V Drive Nch+Nch MOSFET

## **SP8K63**

#### ●Structure

Silicon N-channel MOSFET

#### ● Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small surface Mount Package (SOP8).

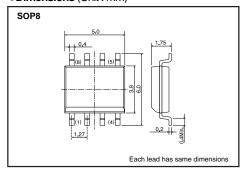
## Application

Switching

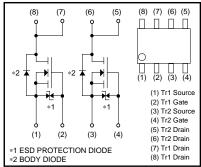
## Packaging specifications

	Package	Taping
Type	Code	TB
	Basic ordering unit (pieces)	2500
SP8K63		0

## ●Dimensions (Unit:mm)



#### •Inner circuit



<sup>\*</sup>A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

### ● Absolute maximum ratings (Ta=25°C) <It is the same ratings for the Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	Continuous	ΙD	±7	А	
	Pulsed	I <sub>DP</sub> *1	±28	А	
Source current	Continuous	Is	1.6	А	
(Body diode)	Pulsed	I <sub>SP</sub> *1	28	Α	
Total power dissipation		Pp *2	2.0	W/TOTAL	
		FD	1.4	W/ELEMENT	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

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## ●Electrical characteristics (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	±10	μΑ	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	30	_	_	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	-	1	μΑ	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V
Gate threshold voltage	VGS (th)	1.0	_	2.5	V	Vps=10V, Ip=1mA
Static drain-source on-state resistance	RDS (on)	-	20	28	mΩ	I <sub>D</sub> =7A, V <sub>GS</sub> =10V
		_	25	35		ID=7A, VGS=4.5V
		-	27	38		I <sub>D</sub> =7A, V <sub>GS</sub> =4.0V
Forward transfer admittance	Y <sub>fs</sub> *	4.5	_	_	S	I <sub>D</sub> =7A, V <sub>DS</sub> =10V
Input capacitance	Ciss	_	1000	_	pF	V <sub>DS</sub> =10V
Output capacitance	Coss	-	150	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	100	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	15	-	ns	I <sub>D</sub> =3.5A, V <sub>DD</sub> ≒15V
Rise time	tr *	_	40	_	ns	Vgs=10V
Turn-off delay time	t <sub>d (off)</sub> *	_	40	_	ns	R <sub>L</sub> =4.29Ω
Fall time	t <sub>f</sub> *	_	15	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	-	8.5	12.8	nC	I <sub>D</sub> =7A, V <sub>DD</sub> ≒15V
Gate-source charge	Q <sub>gs</sub> *	-	2.8	-	nC	V <sub>GS</sub> =5V
Gate-drain charge	Q <sub>gd</sub> *	-	2.8	-	nC	$R_L=2.14\Omega$ , $R_G=10\Omega$

<sup>\*</sup>Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	_	_	1.2	V	I <sub>S</sub> =7A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

#### •Electrical characteristic curves

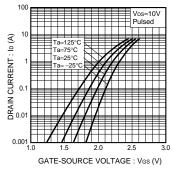


Fig.1 Typical Transfer Characteristics

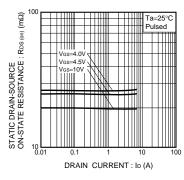


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current ( I )

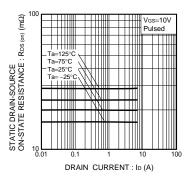


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current(II)

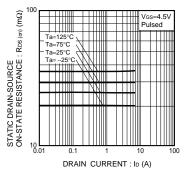


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (III)

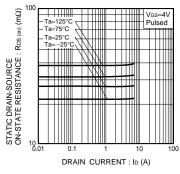


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current (IV)

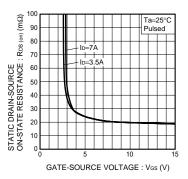


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

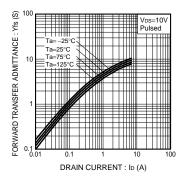


Fig.7 Forward Transfer Adomittance vs. Drain Current

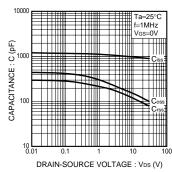


Fig.8 Typical Capacitance vs. Drain-Source Voltage

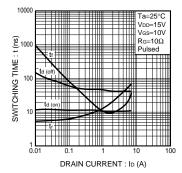


Fig.9 Switching Characteristics

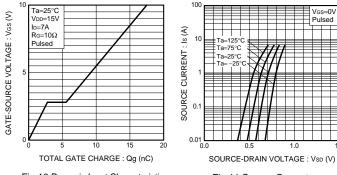


Fig.10 Dynamic Input Characteristics

Fig.11 Source Current vs. Source-Drain Voltage

#### ●Measurement circuit

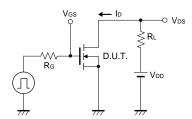


Fig.12 Switching Time Test Circuit

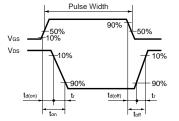


Fig.13 Switching Time Waveforms

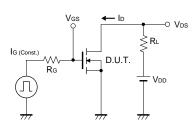


Fig.14 Gate Charge Test Circuit

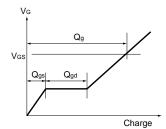


Fig.15 Gate Charge Waveform

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